

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.2V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

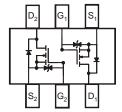
Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.006 grams (Approximate)

SOT563







Top View Schematic and Transistor Diagram

Ordering Information (Note 4)

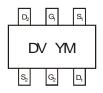
| Part Number | Case | Packaging |
|-------------|--------|-------------------|
| DMN32D2LV-7 | SOT563 | 3,000/Tape & Reel |

Notes:

- $1.\ No\ purposely\ added\ lead.\ Fully\ EU\ Directive\ 2002/95/EC\ (RoHS)\ \&\ 2011/65/EU\ (RoHS\ 2)\ compliant.$
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information

SOT563



DV = Product Type Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Kev

| Year | 2007 | | 20 | 14 | 2015 | 2016 | 2017 | 2018 | 3 20 | 19 | 2020 | 2021 |
|-------|------|-----|-----|-----|------|------|------|------|------|-----|------|------|
| Code | U | | [| 3 | С | D | E | F | (| 3 | Н | ı |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

| Characteristic | Symbol | Value | Unit |
|------------------------|----------------|-------|------|
| Drain Source Voltage | V_{DSS} | 30 | V |
| Gate-Source Voltage | V_{GSS} | ±10 | V |
| Drain Current (Note 5) | I _D | 400 | mA |

Thermal Characteristics

| Total Power Dissipation (Note 5) | P_{D} | 450 | mW |
|--|------------------|-------------|------|
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{\theta JA}$ | 313 | °C/W |
| Operating and Storage Temperature Range | T_{J}, T_{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

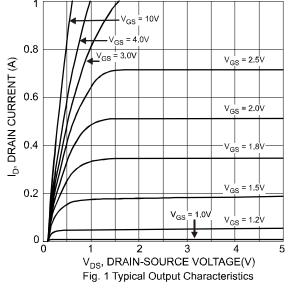
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | | |
|------------------------------------|-------------------------|---------------------|-----|-----|------------|------------------------------|--|--|
| OFF CHARACTERISTICS (Note 6) | | | | | • | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | 30 | _ | _ | V | $V_{GS} = 0V, I_D = 250\mu A$ | |
| Zero Gate Voltage Drain Current | @T _J = +25°C | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 30V, V_{GS} = 0V$ | |
| | | | | _ | ±10 | μΑ | $V_{GS} = \pm 10V$, $V_{DS} = 0V$ | |
| Gate-Body Leakage | $@T_J = +25^{\circ}C$ | I_{GSS} | _ | _ | ±500 | nA | $V_{GS} = \pm 5V$, $V_{DS} = 0V$ | |
| | | | | ±1 | ±100 | nA | $V_{GS} = \pm 2.5V, V_{DS} = 0V$ | |
| Gate-Body Leakage (Note 7) | $@T_J = +105^{\circ}C$ | 1 | | ±8 | ±100 | nA nA | \/ 12 E \/ \/ = 0\/ | |
| | $@T_J = +125^{\circ}C$ | I _{GSS} | _ | ±15 | ±100 | | $V_{GS} = \pm 2.5 V, V_{DS} = 0 V$ | |
| ON CHARACTERISTICS (Note 6) | | | | | | | | |
| Gate Threshold Voltage | | V _{GS(TH)} | 0.6 | _ | 1.2 | V | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | |
| | | R _{DS(ON)} | _ | _ | 2.2 1.5 | | $V_{GS} = 1.8V, I_D = 20mA$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | _ | _ | | Ω | $V_{GS} = 2.5V, I_D = 20mA$ | |
| | | — | _ | 1.2 | | $V_{GS} = 4.0V, I_D = 100mA$ | | |
| Forward Transconductance | | Y _{FS} | 100 | _ | _ | mS | $V_{DS} = 10V, I_D = 0.1A$ | |
| Source-Drain Diode Forward Voltage | | V _{SD} | 0.5 | _ | 1.4 | V | $V_{GS} = 0V, I_{S} = 115mA$ | |
| DYNAMIC CHARACTERISTICS (Note 7) | | | | | | | | |
| Input Capacitance | | C _{ISS} | _ | 39 | _ | pF | ., ., ., ., | |
| Output Capacitance | | Coss | _ | 10 | _ | pF | $V_{DS} = 3V, V_{GS} = 0V$ f = 1.0MHz | |
| Reverse Transfer Capacitance | | | _ | 3.6 | _ | pF | 1 = 1.0IVIDZ | |
| Switching Time | Turn-On Time | t _{ON} | _ | 11 | _ | ns | $V_{DD} = 5V, I_D = 10 \text{ mA},$ | |
| Switching time | Turn-Off Time | toff | _ | 51 | _ | ns | $V_{GS} = 5V$ | |

Notes:

^{5.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found at http://www.diodes.com/datasheets/ap02001.pdf.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.





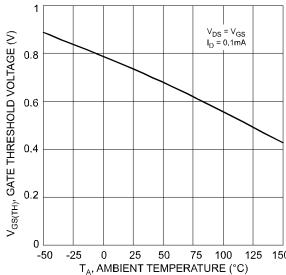


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

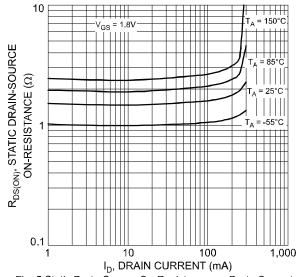
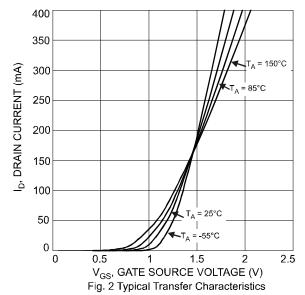


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



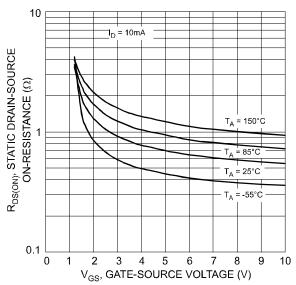


Fig. 4 Static Drain-Source On-Resistance vs. Gate-Source Voltage

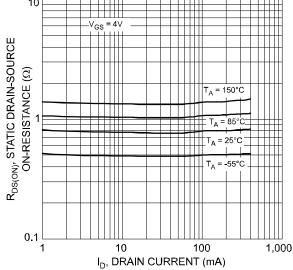
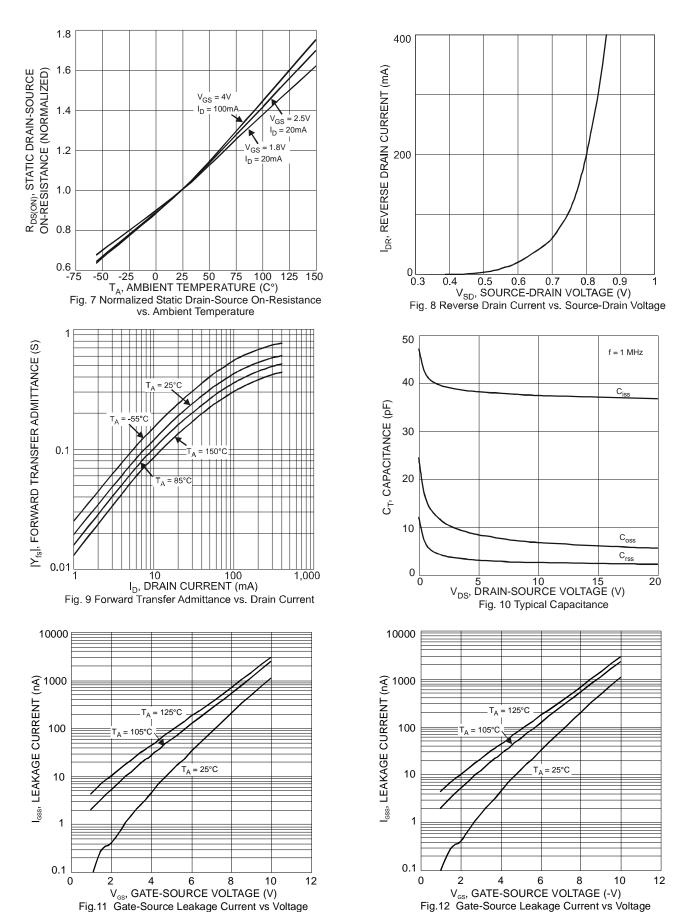


Fig. 6 Static Drain-Source On-Resistance vs. Drain Current



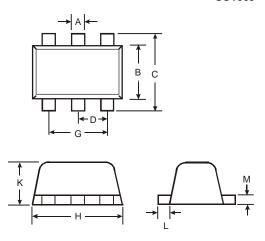




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

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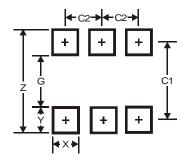


| SOT-563 | | | | | | |
|----------------------|------|------|------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.15 | 0.30 | 0.20 | | | |
| В | 1.10 | 1.25 | 1.20 | | | |
| С | 1.55 | 1.70 | 1.60 | | | |
| D | _ | _ | 0.50 | | | |
| G | 0.90 | 1.10 | 1.00 | | | |
| Н | 1.50 | 1.70 | 1.60 | | | |
| K | 0.55 | 0.60 | 0.60 | | | |
| L | 0.10 | 0.30 | 0.20 | | | |
| М | 0.10 | 0.18 | 0.11 | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT563



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.2 |
| G | 1.2 |
| Х | 0.375 |
| Υ | 0.5 |
| C1 | 1.7 |
| C2 | 0.5 |



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